

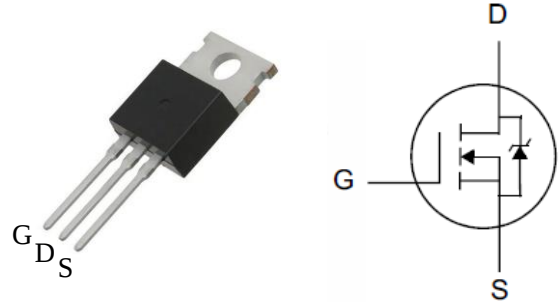
General Features

- Proprietary New Trench Technology
- $R_{DS(ON),typ.}=8.5m\Omega@V_{GS}=10V$
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

BV_{DSS}	$R_{DS(ON),typ.}$	I_D
150V	8.5m Ω	120A

Applications

- DC/DC Converter
- Motor Control
- Synchronous Rectification



TO-220

Package No to Scale

Ordering Information

Part Number	Package
IRFB4115PBF-CN	TO-220

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	IRFB4115PBF-CN	Unit
V_{DSS}	Drain-to-Source Voltage ^[1]	150	V
V_{GSS}	Gate-to-Source Voltage	± 20	
I_D	Continuous Drain Current	120	A
	Continuous Drain Current @ $T_C=100^{\circ}C$	84	
I_{DM}	Pulsed Drain Current at $V_{GS}=10V^{[2]}$	380	
E_{AS}	Single Pulse Avalanche Energy $L=1mH$	450	mJ
P_D	Power Dissipation	208	W
	Derating Factor above $25^{\circ}C$	0.67	W/ $^{\circ}C$
T_L T_{PAK}	Maximum Temperature for Soldering Leads at 0.063in (1.6mm) from Case for 10 seconds, Package Body for 10 seconds	300 260	$^{\circ}C$
$T_J \& T_{STG}$	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	IRFB4115PBF-CN	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.6	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62	

Electrical Characteristics

OFF Characteristics $T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	150	--	--	V	$V_{GS}=0V, I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	--	--	1	μA	$V_{DS}=150V, V_{GS}=0V$
		--	--	100		$V_{DS}=150V, V_{GS}=0V, T_J=125^\circ\text{C}$
I_{GSS}	Gate-to-Source Leakage Current	--	--	+100	nA	$V_{GS}=+20V, V_{DS}=0V$
		--	--	-100		$V_{GS}=-20V, V_{DS}=0V$

ON Characteristics $T_J = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	8.5	10.5	m Ω	$V_{GS}=10V, I_D=20A$
$V_{GS(TH)}$	Gate Threshold Voltage	2.0	--	4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$

Dynamic Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
C_{iss}	Input Capacitance	--	2980	--	pF	$V_{GS}=0V, V_{DS}=75V, f=1.0\text{MHz}$
C_{rss}	Reverse Transfer Capacitance	--	4.0	--		
C_{oss}	Output Capacitance	--	283	--		
R_G	Gate Series Resistance	--	2.0	--	Ω	$f=1.0\text{MHz}$
Q_g	Total Gate Charge	--	39	--	nC	$V_{DD}=75V, I_D=20A, V_{GS}=0 \text{ to } 10V$
Q_{gs}	Gate-to-Source Charge	--	13	--		
Q_{gd}	Gate-to-Drain (Miller) Charge	--	6.8	--		

Resistive Switching Characteristics Essentially independent of operating temperature

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$t_{d(ON)}$	Turn-on Delay Time	--	21	--	ns	$V_{DD}=75V$, $I_D=20A$, $V_{GS}=10V$ $R_G=3.0\Omega$
t_{rise}	Rise Time	--	7.6	--		
$t_{d(OFF)}$	Turn-Off Delay Time	--	37	--		
t_{fall}	Fall Time	--	6.7	--		

Source-Drain Body Diode Characteristics $T_J=25^\circ C$ unless otherwise specified

Symbol	Parameter	Min	Typ.	Max.	Unit	Test Conditions
I_{SD}	Continuous Source Current ^[2]	--	--	120	A	Integral PN-diode in MOSFET
I_{SM}	Pulsed Source Current ^[2]	--	--	380		
V_{SD}	Diode Forward Voltage	--	--	1.2	V	$I_S=40A$, $V_{GS}=0V$
t_{rr}	Reverse recovery time	--	113	--	ns	$V_{GS}=0V$, $I_F=20A$, $di_F/dt=100A/\mu s$
Q_{rr}	Reverse recovery charge	--	141	--	nC	

Note:

[1] $T_J=+25^\circ C$ to $+150^\circ C$.

[2] Repetitive rating; pulse width limited by maximum junction temperature.

[4] Pulse width $\leq 380\mu s$; duty cycle $\leq 2\%$.

Typical Characteristics

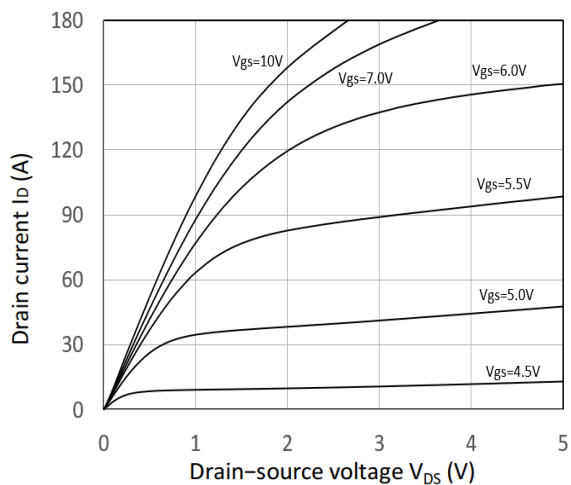


Figure 1. Output Characteristics

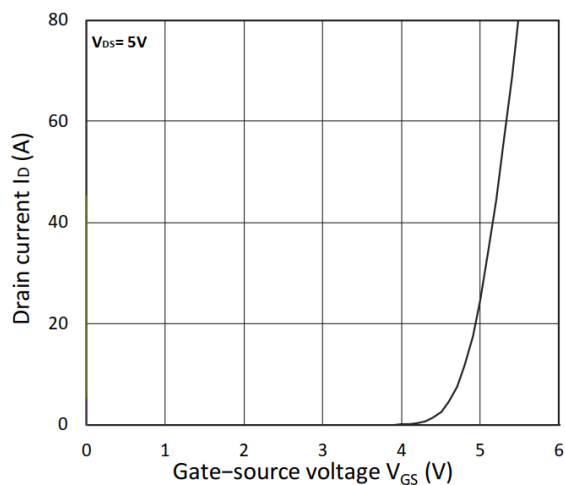


Figure 2. Transfer Characteristics

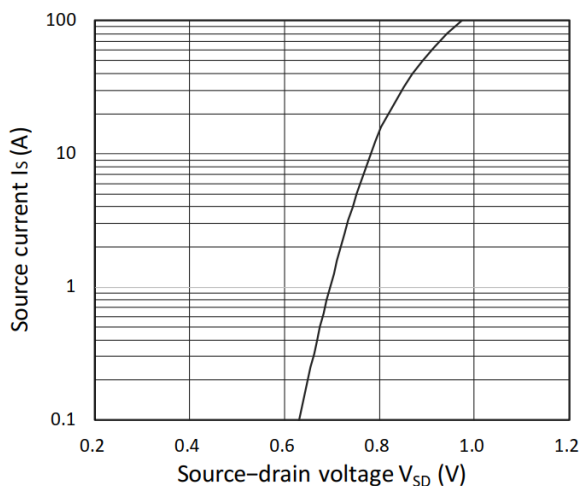


Figure 3. Forward Characteristics of Reverse

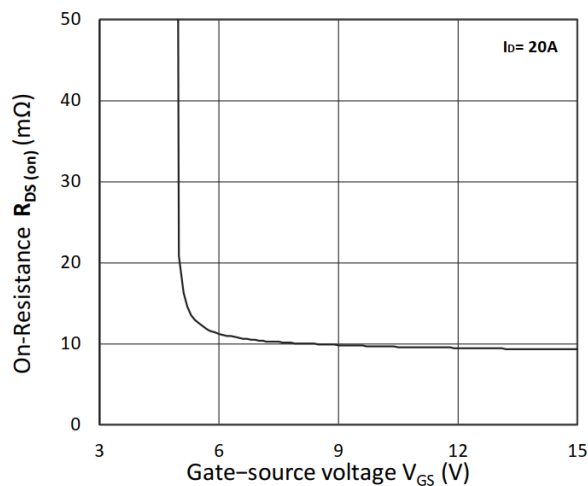


Figure 4. $R_{DS(on)}$ vs. V_{GS}

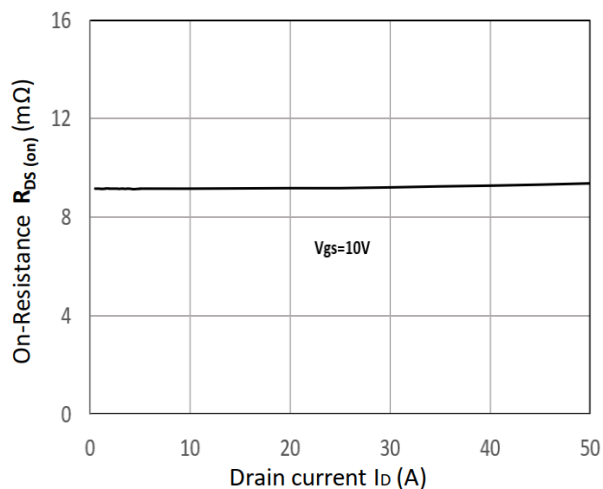


Figure 5. $R_{DS(on)}$ vs. I_D

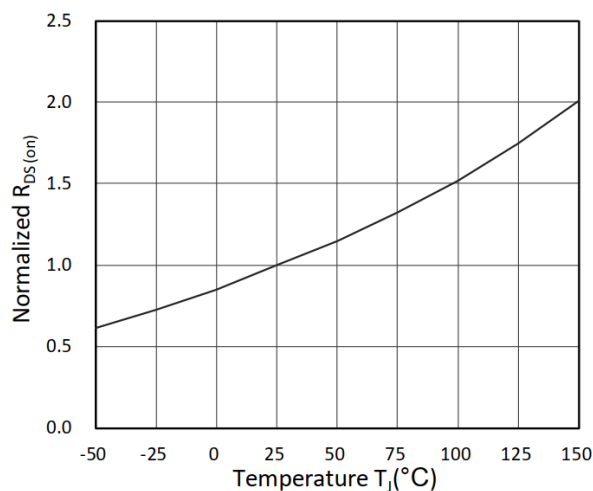


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

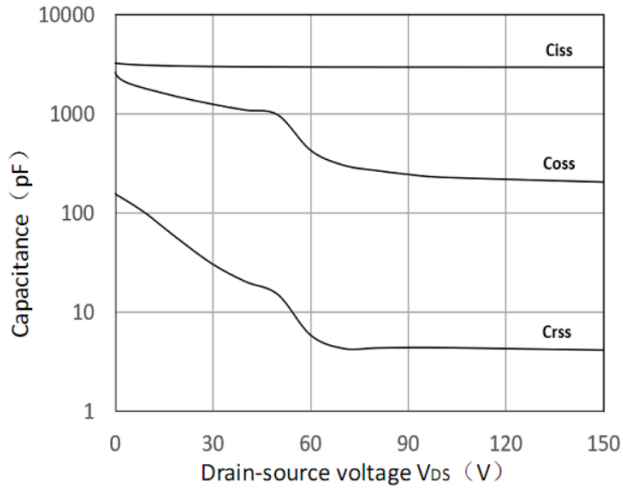


Figure 7. Capacitance Characteristics

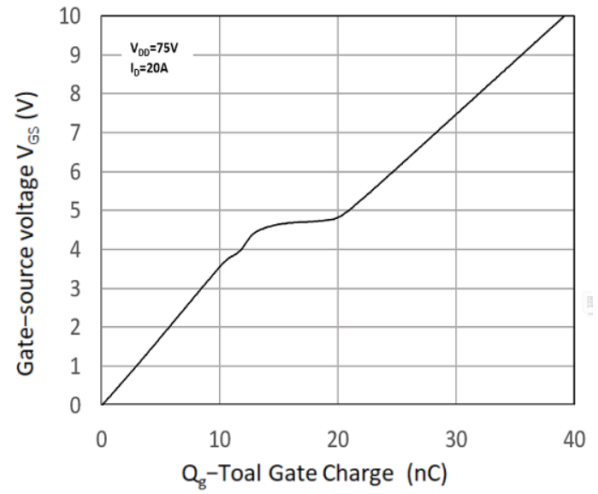


Figure 8. Gate Charge Characteristics

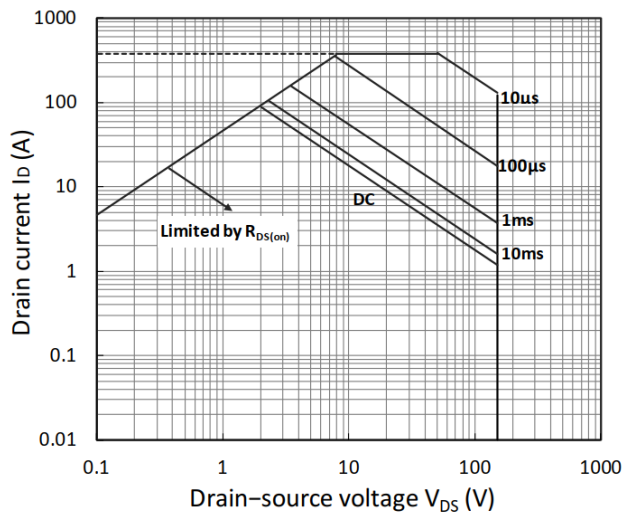


Figure9. Safe Operating Area

Test Circuits and Waveforms

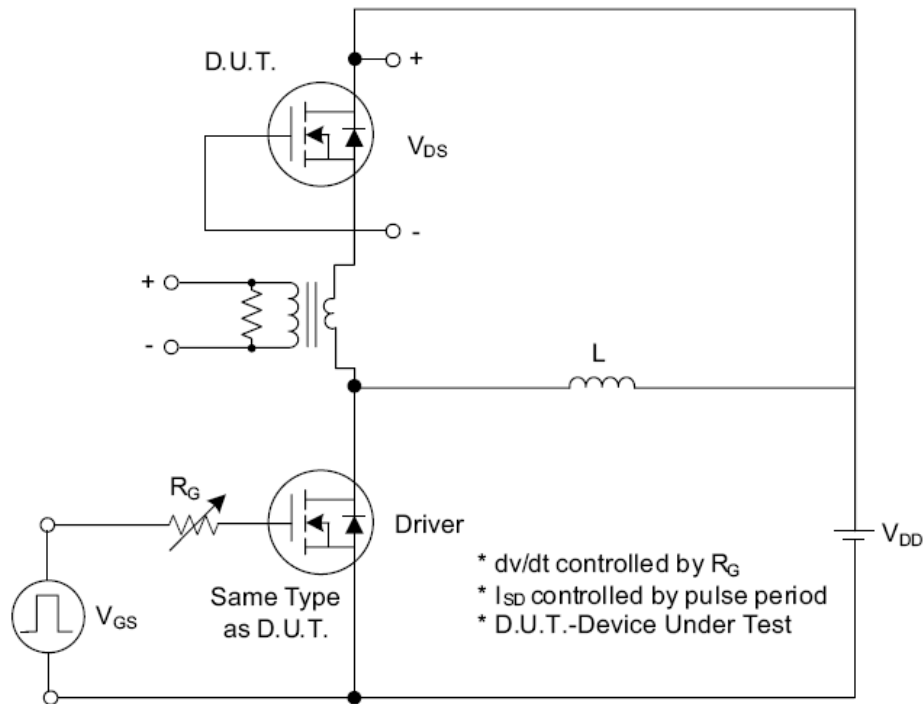


Fig. 1.1 Peak Diode Recovery dv/dt Test Circuit

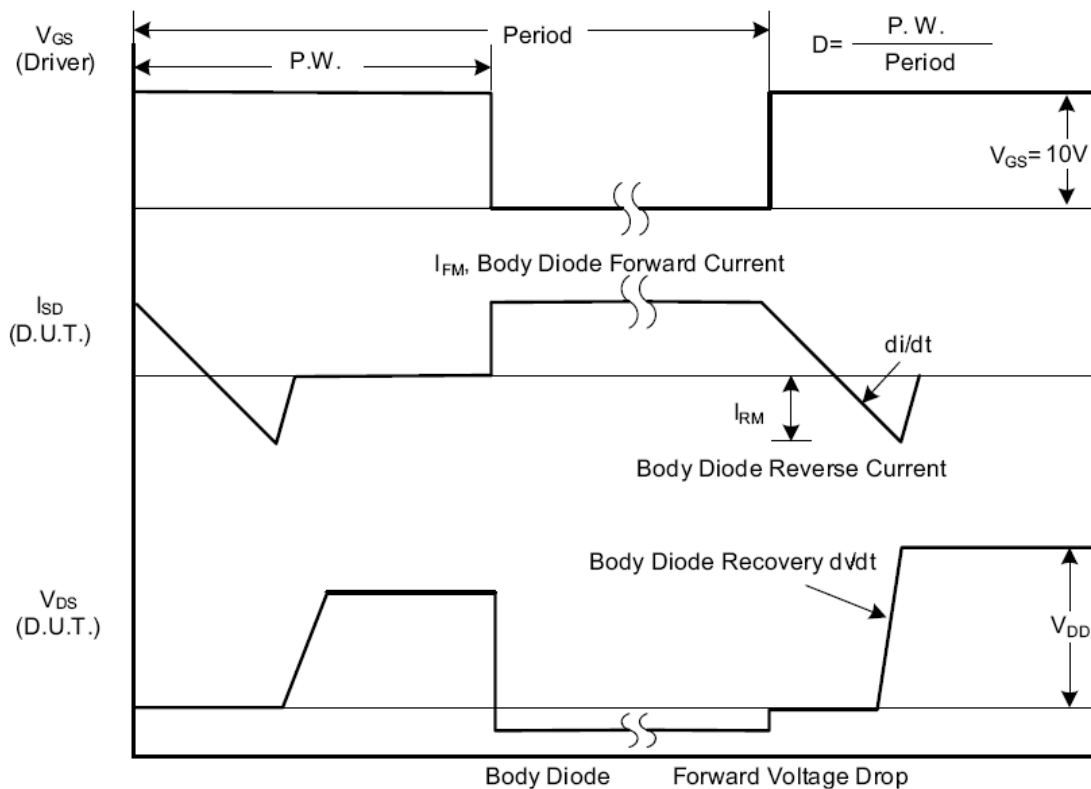


Fig. 1.2 Peak Diode Recovery dv/dt Waveforms

Test Circuits and Waveforms (Cont.)

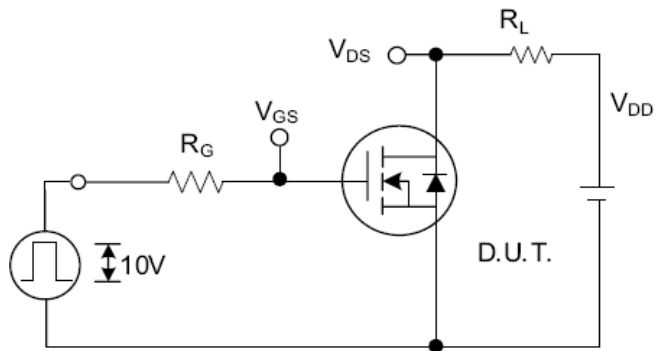


Fig. 2.1 Switching Test Circuit

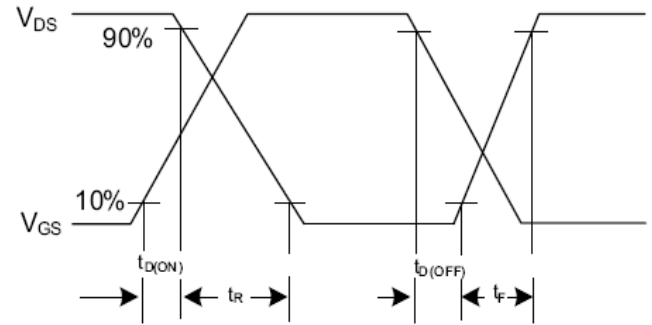


Fig. 2.2 Switching Waveforms

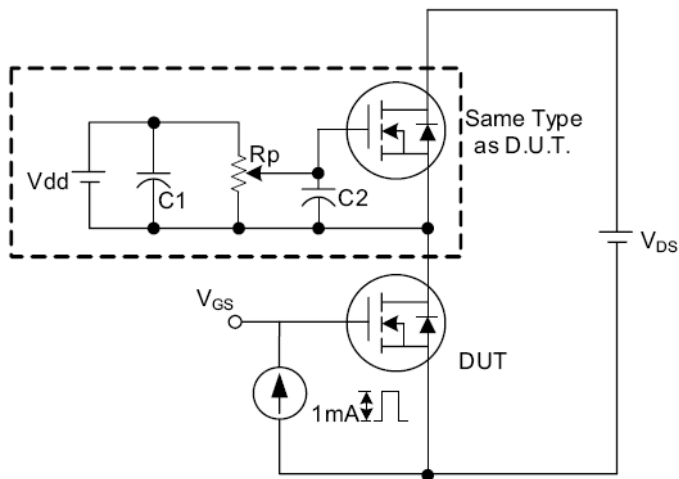


Fig. 3.1 Gate Charge Test Circuit

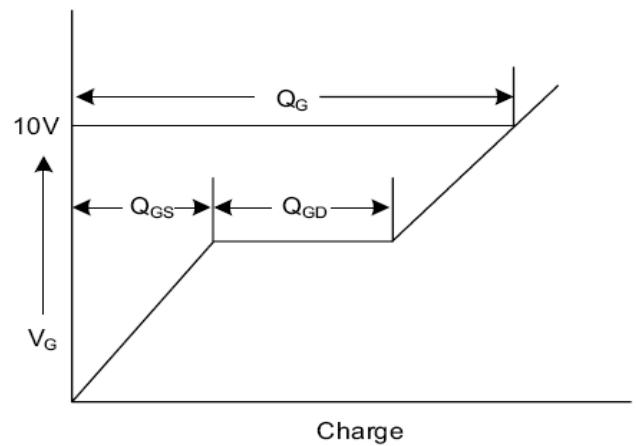


Fig. 3.2 Gate Charge Waveform

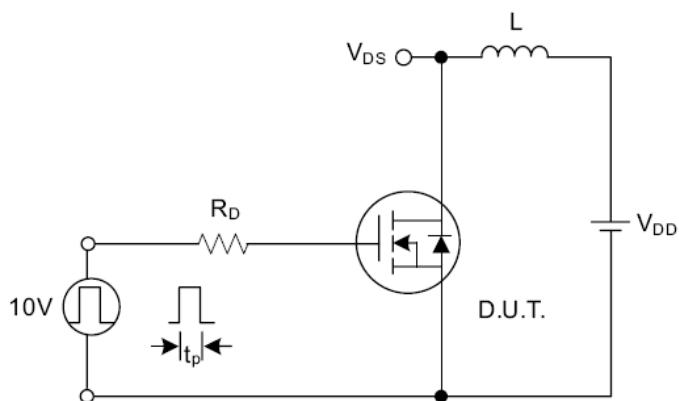


Fig. 4.1 Unclamped Inductive Switching Test Circuit

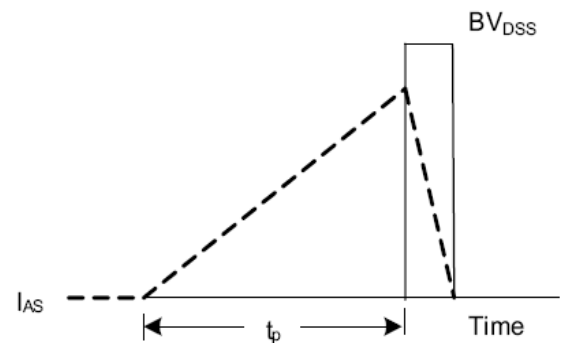


Fig. 4.2 Unclamped Inductive Switching Waveforms

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